

CD4008BMS

CMOS 4-Bit Full Adder With Parallel Carry Out

10 S1

9 C1

November 1994

Features

- · High-Voltage Type (20V Rating)
- 4 Sum Outputs Plus Parallel Look-ahead Carry-Output
- High-Speed Operation Sum In-To-Sum Out, 160ns Typ; Carry In-To-Carry Out, 5ns Typ. At VDD = 10V, CL=50pF
- Standardized Symmetrical Output Characteristics
- 100% Tested For Quiescent Current At 20V
- Maximum Input Current of 1μa at 18V Over Full Package-Temperature Range;
 - 100nA at 18V and 25°C
- Noise Margin (Over Full Package Temperature Range):
 - 1V at VDD = 5V
 - 2V at VDD = 10V
 - 2.5V at VDD = 15V
- 5V, 10V and 15V Parametric Ratings
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications

• Binary Addition/Arithmetic Units

Description

CD4008BMS types consist of four full adder stages with fast look ahead carry provision from stage to stage. Circuitry is included to provide a fast "parallel-carry-out" but to permit high-speed operation in arithmetic sections using several CD4008BMS's.

CD4008BMS inputs include the four sets of bits to be added, A1 to A4 and B1 to B4, in addition to the "Carry In" bit from a previous section. CD4008BMS outputs include the four sum bits, S1 to S4. In addition to the high speed "parallel-carry-out" which may be utilized at a succeeding CD4008BMS section.

The CD4008BMS is supplied in these 16-lead outline packages:

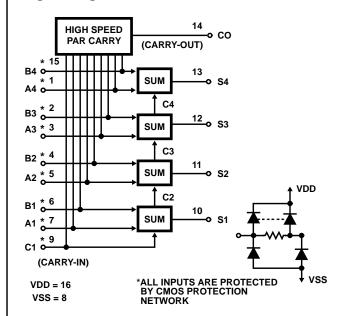
Braze Seal DIP H4T Frit Seal DIP H1F Ceramic Flatpack H6W

CD4008BMS TOP VIEW A4 1 16 VDD B3 2 15 B4 A3 3 14 CO B2 4 13 S4 A2 5 12 S3 B1 6 11 S2

Logic Diagram

A1 7

VSS 8



TRUTH TABLE

A _i	B _i	C _i	c _o	SUM
0	0	0	0	0
1	0	0	0	1
0	1	0	0	1
1	1	0	1	0
0	0	1	0	1
1	0	1	1	0
0	1	1	1	0
1	1	1	1	1

Reliability Information Absolute Maximum Ratings Thermal Resistance nermal Resistance θ_{ja} Ceramic DIP and FRIT Package 80° C/W DC Supply Voltage Range, (VDD) -0.5V to +20V $_{20^{o}\text{C/W}}^{\theta_{jc}}$ (Voltage Referenced to VSS Terminals) Flatpack Package 70°C/W Input Voltage Range, All Inputs -0.5V to VDD +0.5V 20°C/W Maximum Package Power Dissipation (PD) at +125°C DC Input Current, Any One Input±10mA Operating Temperature Range.....-55°C to +125°C For TA = -55° C to $+100^{\circ}$ C (Package Type D, F, K).....500mW Package Types D, F, K, H For TA = $+100^{\circ}$ C to $+125^{\circ}$ C (Package Type D, F, K) Derate Storage Temperature Range (TSTG) -65°C to +150°C Linearity at 12mW/°C to 200mW Lead Temperature (During Soldering) +265°C Device Dissipation per Output Transistor 100mW At Distance 1/16 \pm 1/32 Inch (1.59mm \pm 0.79mm) from case for For TA = Full Package Temperature Range (All Package Types) 10s Maximum

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

				GROUP A		LIM	ITS	
PARAMETER	SYMBOL	CONDITIONS (NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VD	D or GND	1	+25°C	-	10	μΑ
				2	+125°C	-	1000	μΑ
		VDD = 18V, VIN = VD	D or GND	3	-55°C	-	10	μΑ
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load	•	1, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load	VDD = 15V, No Load (Note 3)		+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1	VDD = 15V, VOUT = 1.5V		+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.	.5V	1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9	9.5V	1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 1	13.5V	1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10	μΑ	1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μ/	4	1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = V	DD or GND	7	+25°C	VOH>	VOL <	V
		VDD = 20V, VIN = VD	D or GND	7	+25°C	VDD/2	VDD/2	
		VDD = 18V, VIN = VD	D or GND	8A	+125°C	1		
		VDD = 3V, VIN = VDD	or GND	8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5	VDD = 5V, VOH > 4.5V, VOL < 0.5V		+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13 VOL < 1.5V	VDD = 15V, VOH > 13.5V, VOL < 1.5V		+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being 3. For accuracy, voltage is measured differentially to VDD. Limit implemented.

2. Go/No Go test with limits applied to inputs

is 0.050V max.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

			GROUP A		LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHL1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	800	ns
Sum In to Sum Out	TPLH1		10, 11	+125°C, -55°C	-	1080	ns
Propagation Delay	TPHL2		9	+25°C	-	740	ns
Carry In To Cum Out	TPLH2		10, 11	+125°C, -55°C	-	999	ns
Propagation Delay	TPHL3	VDD = 5V, VIN = VDD or GND	9	+25°C	-	400	ns
Sum In To Carry Out	TPLH3		10, 11	+125°C, -55°C	-	540	ns
Propagation Delay	TPHL4	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
Carry In To Carry Out	TPLH4		10, 11	+125°C, -55°C	-	270	ns
Transition Time	TTHL	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
	TTLH		10, 11	+125°C, -55°C	-	270	ns

NOTES:

- 1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIN	MITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	μΑ
				+125°C	-	150	μΑ
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μΑ
				+125°C	-	300	μΑ
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	μΑ
				+125°C	-	600	μΑ
Output Voltage	VOL	VDD = 5V, No Load	DD = 5V, No Load 1, 2 +25°C, +125°C -55°C		-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	DD = 10V, No Load 1, 2 +25°C, +125°C -55°C		-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	VDD = 5V, No Load 1, 2 +25°C, +125°C, -55°C		4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Output Current (Source)	IOH10 VDD = 10V, VOUT = 9.5V		1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay Sum	TPHL1	VDD = 10V	1, 2, 3	+25°C	-	320	ns
In To Sum Out	TPLH1	VDD = 15V	1, 2, 3	+25°C	-	230	ns
Propagation Delay Carry	TPHL2	VDD = 10V	1, 2, 3	+25°C	-	310	ns
In To Sum Out	TPLH2	VDD = 15V	1, 2, 3	+25°C	-	230	ns
Propagation Delay Sum	TPLH3	VDD = 10V	1, 2, 3	+25°C	-	180	ns
In To Carry Out	TPHL3	VDD = 15V	1, 2, 3	+25°C	-	130	ns
Propagation Delay Carry	TPHL4	VDD = 10V	1, 2, 3	+25°C	-	100	ns
In To Carry Out	TPLH4	VDD = 15V	1, 2, 3	+25°C	-	80	ns
Transition Time	TTHL	VDD = 10V	1, 2, 3	+25°C	-	100	ns
	TTLH	VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	μΑ
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVPTH	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH >	VOL <	V
		VDD = 3V, VIN = VDD or GND			VDD/2	VDD/2	

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIMITS		
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test	1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test	2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note	e 1)	100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1.5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

	MIL-STD-883	TE	TEST		RECORD
CONFORMANCE GROUPS	METHOD	PRE-IRRAD POST-IRRAD		PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

					OSCILLATOR	
FUNCTION	OPEN	GROUND	VDD	9V \pm -0.5V	50kHz	25kHz
Static Burn-In 1 Note 1	10 - 14	1 - 9, 15	16			
Static Burn-In 2 Note 1	10 - 14	8	1 - 7, 9, 15, 16			
Dynamic Burn- In Note 1	-	8	16	10 - 14	2, 4, 6, 15	1, 3, 5, 7, 9
Irradiation Note 2	10 - 14	8	1 - 7, 9, 15, 16			

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

					OSCILLATOR	
FUNCTION	OPEN	GROUND	VDD	9V \pm -0.5V	50kHz	25kHz

NOTE:

- 1. Each pin except VDD and GND will have a series resistor of 10K \pm 5%, VDD = 18V \pm 0.5V
- 2. Each pin except VDD and GND will have a series resistor of $47K \pm 5\%$; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = $10V \pm 0.5V$

Typical Propagation Delay

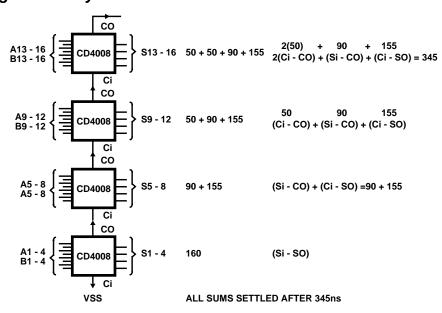


FIGURE 1. PROPAGATION DELAY FOR A 16 BIT ADDER (10V OPERATION)

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Typical Performance Characteristics

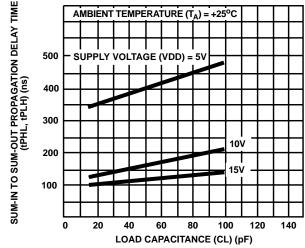


FIGURE 2. TYPICAL SUM-IN TO SUM-OUT PROPAGATION DELAY TIME vs LOAD CAPACITANCE

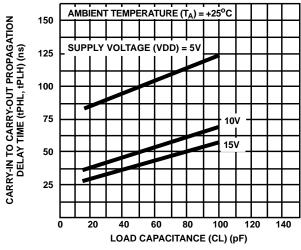


FIGURE 3. TYPICAL CARRY-IN TO CARRY-OUT PROPAGA-TION DELAY TIME vs LOAD CAPACITANCE

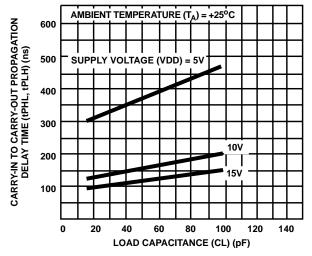


FIGURE 4. TYPICAL CARRY-IN TO SUM-OUT PROPAGATION DELAY TIME vs LOAD CAPACITANCE

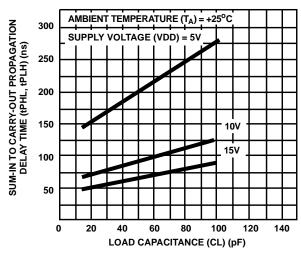


FIGURE 5. TYPICAL SUM-IN TO CARRY-OUT PROPAGATION DELAY TIME vs LOAD CAPACITANCE

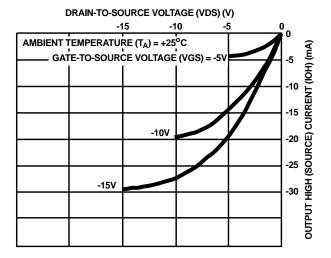


FIGURE 6. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

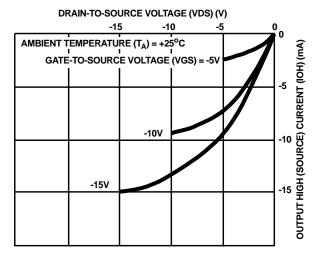


FIGURE 7. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

Typical Performance Characteristics (Continued)

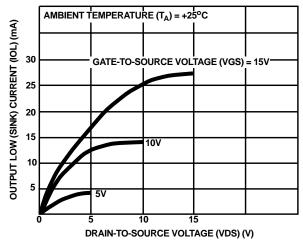


FIGURE 8. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

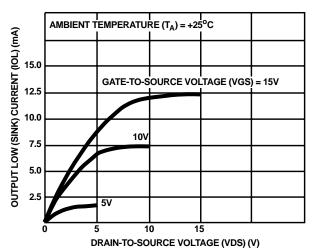


FIGURE 9. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

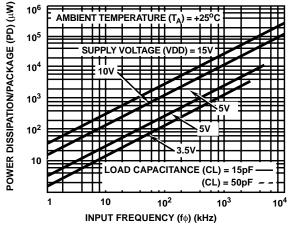
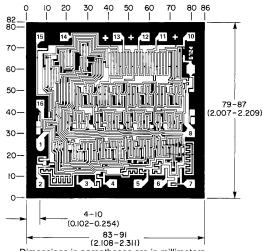


FIGURE 10. TYPICAL DISSIPATION CHARACTERISTICS

Chip Dimensions and Pad Layouts



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch)

METALLIZATION: Thickness: 11kÅ – 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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